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Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave silicon gate-controlled devices are needed.

Features

- Blocking Voltage to 800 Volts
- On-State Current Rating of 12 Amperes RMS at 80°C
- High Surge Current Capability 100 Amperes
- Rugged, Economical TO-220AB Package
- Glass Passivated Junctions for Reliability and Uniformity
- Minimum and Maximum Values of IGT, VGT an IH Specified for Ease of Design
- High Immunity to dv/dt 100 V/usec Minimum at 125°C
- These are Pb-Free Devices

MAXIMUM RATINGS (T_{.I} = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (T _J = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	$V_{ m DRM,} \ V_{ m RRM}$		V
MCR12DG MCR12MG MCR12NG		400 600 800	
On-State RMS Current (180° Conduction Angles; T _C = 80°C)	I _{T(RMS)}	12	Α
Peak Non-repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T _J = 125°C)	I _{TSM}	100	Α
Circuit Fusing Consideration (t = 8.33 ms)	I ² t	41	A ² sec
Forward Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 80°C)	P _{GM}	5.0	W
Forward Average Gate Power $(t = 8.3 \text{ ms}, T_C = 80^{\circ}\text{C})$	P _{G(AV)}	0.5	W
Average On-State Current (180° Conduction Angles; T _C = 80°C)	I _{T(AV)}	7.8	Α
Forward Peak Gate Current (Pulse Width \leq 1.0 μ s, T _C = 90°C)	I _{GM}	2.0	Α
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

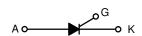
 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



ON Semiconductor®

www.onsemi.com

SCRs 12 AMPERES RMS 400 thru 800 VOLTS



MARKING DIAGRAM





TO-220 CASE 221A-09 STYLE 3

= Assembly Location

Y = Year
WW = Work Week
x = D, M, or N
G = Pb-Free Package
AKA = Diode Polarity

PIN ASSIGNMENT		
1	Cathode	
2	Anode	
3	Gate	
4	Anode	

ORDERING INFORMATION

Device	Package	Shipping
MCR12DG	TO-220AB (Pb-Free)	50 Units / Rail
MCR12MG	TO-220AB (Pb-Free)	50 Units / Rail
MCR12NG	TO-220AB (Pb-Free)	50 Units / Rail

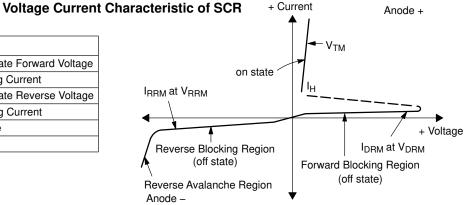
THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient	$R_{ heta JC} \ R_{ heta JA}$	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
$\label{eq:peak_repetitive} \begin{array}{ll} \text{Peak Repetitive Forward or Reverse Blocking Current} \\ (V_D = \text{Rated V}_{DRM} \text{ and V}_{RRM}; \text{ Gate Open)} & T_J = 25^{\circ}\text{C} \\ T_J = 125^{\circ}\text{C} \end{array}$	I _{DRM} , I _{RRM}	_ _	_ _	0.01 2.0	mA
ON CHARACTERISTICS					
Peak Forward On–State Voltage (Note 2) (I _{TM} = 24 A)		-	-	2.2	V
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}$; $R_L = 100 \Omega$)		2.0	8.0	20	mA
Holding Current (V _D = 12 V, Gate Open, Initiating Current = 200 mA)		4.0	20	40	mA
Latch Current (V _D = 12 V, I _G = 20 mA)		6.0	25	60	mA
Gate Trigger Voltage (Continuous dc) (V_D = 12 V; R_L =100 Ω)		0.5	0.65	1.0	V
DYNAMIC CHARACTERISTICS					
Critical Rate of Rise of Off–State Voltage (V _D = Rated V _{DRM} , Exponential Waveform, Gate Open, T _J = 125°C)		100	250	-	V/μs
Repetitive Critical Rate of Rise of On–State Current IPK = 50 A, Pw = 40 μsec, diG/dt = 1 A/μsec, lgt = 50 mA		-	-	50	A/μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Indicates Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

Symbol Parameter Peak Repetitive Off State Forward Voltage V_{DRM} Peak Forward Blocking Current I_{DRM} V_{RRM} Peak Repetitive Off State Reverse Voltage Peak Reverse Blocking Current I_{RRM} V_{TM} Peak On State Voltage I_H Holding Current



+ Current

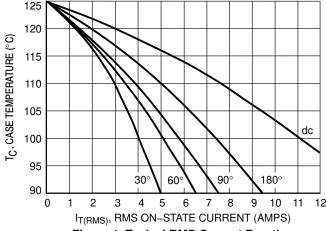


Figure 1. Typical RMS Current Derating

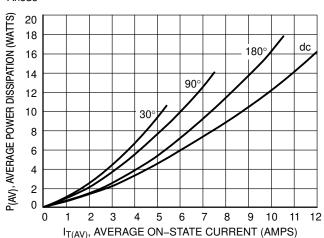


Figure 2. On-State Power Dissipation

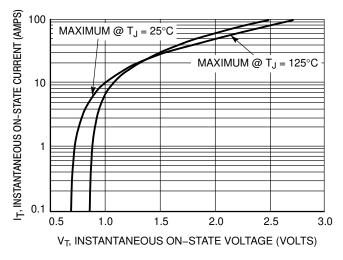


Figure 3. Typical On-State Characteristics

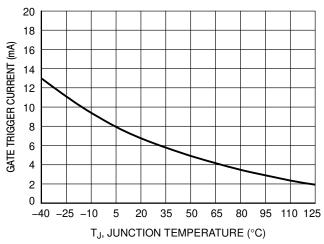


Figure 4. Typical Gate Trigger Current versus Junction Temperature

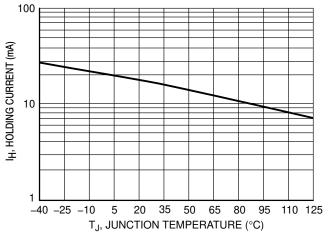


Figure 5. Typical Holding Current versus Junction Temperature

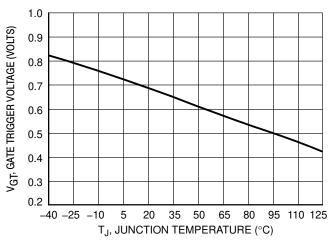


Figure 6. Typical Gate Trigger Voltage versus
Junction Temperature

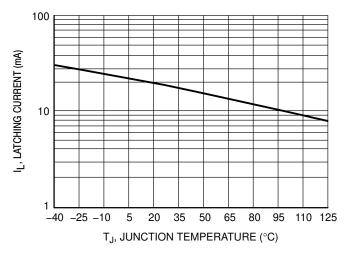
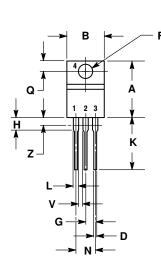
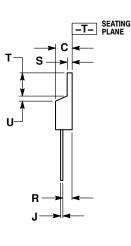


Figure 7. Typical Latching Current versus Junction Temperature

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**





NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
_	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Ø	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 3:

PIN 1. CATHODE

- 2. ANODE
- GATE
- ANODE

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